High harmonic generation (HHG), the frequency conversion of an ac electric field, plays a key role in high-speed electronics at terahertz (THz) frequencies as well as in ultrafast photonics. Recent discoveries of material-based HHG have facilitated the search of the best system for high conversion efficiency. Here we report the appearance of strong THz range third harmonics in thin films of Cd$_3$As$_2$, a three-dimensional Dirac semimetal with linearly dispersing electronic states. THz pump-THz probe spectroscopy gives evidence for the microscopic mechanism originating in the coherent acceleration of Dirac electrons in momentum space as theoretically anticipated. The extreme conversion efficiency, which is detectable using only a tabletop THz source and exceeds that of graphene by over a factor of 100 times, paves the way toward novel devices for ultrafast THz electronics and photonics based on topological semimetals.
One of the major advances in modern photonics is the realization of intense phase-stable light fields, which have revealed highly-intriguing nonlinear and nonperturbative light-matter interactions in atomic or molecular gases and condensed matters. A prominent example is high harmonic generation (HHG), e.g., the production of coherent high-energy photons by multiplication of an incident photon energy, which has been developed in gaseous media for attosecond science (1) and has also been utilized for high-resolution angle-resolved photoemission spectroscopy (ARPES) (2). More recently, HHG in semiconductors with mid-infrared (IR) excitation has been reported (3, 4), opening a new route toward laser-based stable and compact soft X-ray sources.

Efficient third harmonic generation (THG) at the terahertz (THz) frequency regime has been also reported in a superconducting film resonating with a collective mode (5). Realization of such efficient THz frequency conversion at room temperature is highly desired for high-speed electronics. From this perspective, graphene has attracted tremendous attention as a candidate for efficient THz frequency multiplication because the current flow of massless electrons across the Dirac node in momentum space is expected to exhibit remarkably large nonlinearity (6-13). THz HHG in graphene has, however, long evaded experimental detection. A signature was first reported in a sample consisting of 45-layer graphene at cryogenic temperature (14). The difficulty of observing THz HHG in graphene has been attributed to fast carrier scattering, which hampers coherent carrier transport at THz timescales (15), and thus, attention has been shifted to HHG by mid-IR excitation at higher light frequency that exceeds the scattering rate (16-19). THz THG was observed in two-dimensional (2D) Dirac systems such as the surface state of a topological insulator Bi$_2$Se$_3$ (20). Very recently, THz HHG in graphene was clearly demonstrated with nonlinear coefficients much larger than typical materials (21). The conversion efficiency in graphene is, however, limited by its monolayer nature and therefore the observation of THz HHG has required very intense light sources based on large accelerators (20, 21). Therefore, realizing higher conversion efficiency in a bulk material is extremely desired for practical application. Another issue to be resolved is the origin of THz HHG in graphene (21), which was explained by a thermodynamic model where electrons are assumed to be in quasi-equilibrium with repeating heating/cooling processes very rapidly within THz timescale (22). Such a picture of incoherent electron dynamics is an essentially different mechanism from that originally proposed as a source of large nonlinearities in massless Dirac systems (6-13). Getting deeper insight into the microscopic dynamics of Dirac electrons in the high field regime under the influence of scattering is essential as well as is finding other bulk candidates for efficient THz HHG.

Here we investigate THz nonlinear transmission in thin films of the three-dimensional (3D) Dirac semimetal Cd$_3$As$_2$ and report the observation of THz harmonic generation (Fig. 1A) that is much stronger than graphene to the extent that it is observable with a tabletop source at room temperature. We also perform time-resolved THz spectroscopy to reveal the ultrafast
dynamics of Dirac fermions during the THG process. These results provide evidence for the remarkable THz nonlinearity originating from coherent intraband acceleration of Dirac electrons, which has been anticipated theoretically but not demonstrated previously in experiments. We also show efficient HHG by mid-IR excitation in the thin films. Our results show the path forward to design efficient frequency-conversion devices in a wide range of wavelengths that are based on the remarkable features of massless Dirac electrons.

Samples consisted of (112) Cd$_3$As$_2$ thin films with 240-nm thickness epitaxially grown on a GaSb buffer layer on a GaAs substrate. Figure 1C shows the band structure of Cd$_3$As$_2$ calculated in a simple model, which has two Dirac nodes near the Γ point and quasi-linear band dispersion up to the energy scale of ~1 eV. Considering the low concentration and the small effective mass of carriers, the Fermi energy is estimated to be as small as ~50 meV above the Dirac nodes. We performed THz time-domain spectroscopy to evaluate the linear response. See Supplementary Materials for details on sample preparation and measurements. Figure 1D shows the temperature dependence of the real THz conductivity $\sigma_1(\omega)$ for a 240-nm film. The data are reasonably fitted with the Drude model, corresponding to intraband transition of electrons in the conduction band. The inset shows the scattering time $\tau$ obtained from the fitting as a function of temperature. $\tau$~145 fs at 300 K is longer than usual metals and graphene. Such coherent transport is often observed in 3D Dirac or Weyl semimetals with prohibited backward scattering. Interestingly, $\tau$ becomes shorter at low temperatures. This temperature dependence is counterintuitive in usual metals but might be ascribed to a peculiar scattering mechanism of Dirac electrons; if long-range Coulomb impurity potentials dominate the scattering, they are screened more effectively by electrons at higher temperature. In graphene such a temperature dependence to $\tau$ has been observed only in ultraclean suspended samples with the Fermi energy finely tuned to the Dirac point. In this regard, our high-quality Dirac film provides an excellent platform to study intrinsic dynamics of 3D Dirac fermions, which is sometimes obscured in graphene by the faster scattering and inevitable interaction with a substrate.

Figure 1E shows power spectra of an intense THz pulse centered at $f=\omega/2\pi=0.8$ GHz after transmitting through the sample. The peak electric field $E_{\text{pump}}$ is 31 kV/cm in atmosphere and is reduced to 6.5 kV/cm inside the film. THG at 3$f=2.4$ GHz is clearly observed, and a tiny peak of fifth harmonics at 5$f=4.0$ GHz may be also discerned. Clearer data of the fifth harmonics are shown in Supplementary Materials. For comparison, we examined monolayer graphene on a SiC substrate and also found the THG signal there as well. In contrast, a reference substrate of GaSb/GaAs shows no THG. Figure 1F shows the THG intensity as a function of the intensity of transmitted fundamental wave $I$. As plotted with the solid lines in Fig. 1F, THG in Cd$_3$As$_2$ scales as $\sim I^{2.7}$ and $\sim I^{2.4}$ for weaker and stronger field regimes, respectively, showing nonperturbative behavior. For graphene, the THG intensity also saturates at the strong excitation, and in the perturbative regime we estimated the nonlinear coefficient...
χ(3) as ~10^{-9} \text{ m}^2\text{V}^{-2}. These results for graphene are consistent with the previous literature reporting χ(n) to be 7-18 orders of magnitude larger than typical materials (21). Conversion efficiency, the ratio of the THG intensity to the transmitted fundamental wave, is ~10^{-6} in graphene for the applied field of 31 kV/cm in air. On the other hand, the THG in the 240-nm Cd₃As₂ film reaches 10^{-4}, more than 100 times stronger than graphene for the same pump field condition.

To explore the microscopic picture of the efficient HHG mechanism in Cd₃As₂, we performed two types of THz pump-THz probe spectroscopy (TPTP) to investigate the electron dynamics (27). Figure 2A shows a schematic of TPTP with a broadband short pump pulse with a maximum peak field of 50 kV/cm in air and center frequency of 2 THz (27). Figure 2B shows the probe THz waveform E_{probe} as a function of the probe delay t₂ against the gate pulse for the electro-optic sampling. Figure 2C shows a 2D plot of the change of the probe waveform by THz pump, δE_{probe}. With fixing t₂ at the peak of the probe pulse, we plot δE_{probe} as a function of the pump delay t₁ in Fig. 2D, which provides information of ultrafast dynamics induced by the THz pump. δE_{probe} grows just after the pump arrives and then decays slowly. The small dip at t₁~8 ps originates from the reflected THz pump pulse from the back surface of the substrate. Here the probe polarization is perpendicular to the pump (E_{probe}//E_{pump}), but we confirmed that the result is similar with the case of E_{probe}⊥E_{pump} (27). By Fourier transformation, the time evolution of the conductivity spectra σ(ω, t₁) is obtained in Fig. 2E. Figures 2F and 2G show the real and imaginary parts at t₁=5 ps. Except for the very fast timescale within the pump pulse duration (t₁<2 ps), the conductivity spectra are reasonably fitted by the Drude model, and the fitting parameters of the scattering time τ and the carrier density N are plotted in Figs. 2H and 2I as a function of t₁. The increase of N implies that electrons in the valence band are excited to the conduction band by the THz pump. According to the increase of the carrier density and electron temperature, τ also increases and then slowly decays. It can be accounted for by the screening effect of long-range Coulomb impurity scattering and is consistent with the temperature dependence of the equilibrium results. By fitting the relaxation of carrier density with an exponential decay considering multiple reflections of the pump pulses, the relaxation time was evaluated to be ~8 ps, which is much longer than that in graphene (< 1 ps) (32) and consistent with - or a bit longer than - previous pump-probe studies for Cd₃As₂ with near- and mid-IR excitation (33-35).

Since the relaxation time of ~8 ps is much longer than our pump THz field cycle, the efficient THG in our sample cannot be explained by the thermodynamic model assuming rapid heating and cooling processes (21). Usually, non-thermal HHG mechanisms in solids have been discussed in terms of the interband polarization and intraband current (4). The contribution of interband polarization on HHG, which might be dominant in semiconductors with mid-IR excitation, cannot dominate for THz frequencies since the dephasing time is much shorter than the field cycle (36,37). The interband transition could occur in the Dirac semimetal
with supplying additional population of carriers to contribute nonlinear current. However, the increase of the carrier density observed in Fig. 2H was only 20% even for the broadband intense pump pulse because the Fermi energy of ~50 meV is larger than the incident THz photon energy (~several meV). Therefore, we conclude that the interband transition is not a major effect for efficient THG. A similar situation in a doped Dirac system has been discussed in a previous calculation (12).

Our result strongly indicates that the intraband current of accelerated electrons is the main source of the extremely efficient THG. One might think that such a nonlinear current from coherently accelerated electrons would be significantly suppressed by the scattering since the scattering rate $1/\tau \sim 7$ THz is much faster than the pump frequency of 0.8 THz. However, such an influence of the scattering on HHG has been studied in previous theoretical works (12), and HHG has been expected to appear efficiently when the THz field is as strong as a few kV/cm inside the material. Figure 3A shows our calculation of the HHG spectrum considering only the intraband acceleration in a simple linear dispersion model with the scattering time of 145 fs (27). For a few-kV/cm field strength, the THG appears strongly as the ratio to the transmitted fundamental wave reaches $\sim 10^2$ in amplitude ($10^4$ in power). Even such a simple model reasonably reproduces our observation in Fig. 1E. Figure 3B shows the calculated THG amplitude as a function of incident field strength with various scattering time $\tau$. For a longer $\tau$, the saturation occurs at weaker field, which also agrees with the nonperturbative THG in Fig. 1E. Such a saturation is closely related to the Dirac dispersion; when most part of electrons are accelerated across the Dirac node, the current saturates at stronger fields because the electron velocity at larger momentum is constant in linear dispersion. As a result, lower-order harmonics easily saturate in Dirac systems. Figure 3C show the THG amplitude as a function of $\tau$ for the peak fields of 3 and 6 kV/cm and the driving frequency of 0.8 THz. When $\tau$ is shorter than ~50 fs, the THG amplitude is significantly suppressed by fast scattering processes. If $\tau$ is longer than ~100 fs, however, it strongly saturates and behaves as if in the long-$\tau$ limit. Therefore, the result of our calculation shows that $\tau \sim 150$ fs in this material is “long enough” for intraband acceleration driven by a few-kV/cm field at 0.8-THz frequency. Figure 3D shows the 2D plot of electron distribution in the momentum space driven by the field in comparison with equilibrium. A few-kV/cm THz field induce substantial unbalance of the intraband electron distribution in the pump polarization direction, which has been also recently demonstrated in a time-resolved ARPES in a topological insulator (38).

To obtain further insight into the dynamical evolution during the THz THG process, we also performed another TPTP with monochromatic pump waveform as schematically shown in Fig. 3E. Figure 3F shows the pump waveform with $f=0.8$ THz and the change of the probe field $\delta E_{\text{probe}}$ as a function of $t_1$ during the monochromatic pump irradiation. For the case of $E_{\text{probe}}//E_{\text{pump}}$, an oscillation signal is discerned on the slow-rising incoherent carrier excitation. Figure 3G shows its Fourier component with a peak frequency at 1.6 THz. This result means
that the THz conductivity oscillates in time with the frequency $2f$ during the pump irradiation. Such a coherent oscillation under a phase-stable pump field can be observed generally in pump-probe experiments with subcycle time resolution (39). Note that the “$2f$-oscillation” in the pump-probe signals directly corresponds to the THG in the transmission of the pump because the nonlinear $3f$ current arises from the oscillating conductivity with frequency $2f$ (27), as also observed in superconductors (5). Importantly, for the case of $E_{\text{probe}} \perp E_{\text{pump}}$, the $2f$-oscillation signal is hardly seen in time domain and quite small compared to the case of $E_{\text{probe}}/E_{\text{pump}}$. This is in stark contrast to the case of superconductors (5), where the $2f$-oscillation was clearly observed in $E_{\text{probe}} \perp E_{\text{pump}}$; there it is because the $s$-wave order parameter oscillates in time, which results in the isotropic change of the conductivity (40). If the THG is described by the thermodynamic model (21), the change of the conductivity should be also isotropic. Our results for Cd$_3$As$_2$ are, however, clearly distinct from these models.

The probe polarization dependence for the $2f$-oscillation strongly indicates that the THz THG originates from the coherent intraband current. When electrons are accelerated by the pump field without any scattering, they move rapidly back and forth in the momentum space along with the pump polarization direction, but it appears as if "nothing happens" in other probe polarization directions as long as the dispersion is isotopic. Our TPTP experiments resolving the subcycle dynamics within the oscillating pump field is a powerful complementary probe of THz HHG, and the anisotropy for the $2f$-oscillation observed here provides solid evidence for highly-nonlinear current arising from coherently accelerated electrons in momentum space. We revealed that remarkable THz nonlinearity manifests itself with scattering time over 100 fs at room temperature. Even longer scattering times might be achieved in other topological semimetals with massless dispersion, which will show even stronger frequency conversion perhaps in sub-kV/cm field strength.

Finally, we also show that the efficient HHG is observed at near-IR and visible frequencies with mid-IR (4 μm) excitation in reflection geometry, as schematically shown in Fig. 4A (27). Figure 4B shows the observed spectra of the Cd$_3$As$_2$ film compared with that of a bare GaAs substrate and that of a GaAs substrate with only the buffer layer GaSb film. Bare GaAs shows HHG and a strong photoluminescence (PL) peak. When a GaSb layer is on the substrate, even-order harmonics are also strongly observed. When the Cd$_3$As$_2$ film is measured, the PL and the even-order signals are significantly suppressed. For the film as thick as 280 nm, only the odd-order HHG was observed to be stronger than that of the substrate. The results ensure that the strong odd-order HHG up to 11th order undoubtedly arises from the Cd$_3$As$_2$ thin film. We could not observe any signature of even-order HHG for any polarization direction in the (112) surface, which supports the presence of inversion symmetry in Cd$_3$As$_2$ as a Dirac semimetal. Since substantial part of the incident light is reflected from the surface of thin film, antireflection coating with optimized film thickness will further enhance the conversion.
efficiency which could lead to develop a novel frequency convertor in a wide range of frequency based on Dirac semimetals.

References and Notes:

27. Supplementary Materials are available on Science Onliner.


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Fig. 1. Extremely efficient THz HHG in Dirac semimetal Cd$_3$As$_2$. (A) Schematic of the HHG in Dirac electron system. (B) Atomic configuration of (112) Cd$_3$As$_2$ surface. (C) Calculated band structure of Cd$_3$As$_2$ around the Γ point. (D) Real-part THz conductivity spectrum at various temperature (1 THz ~ 4 meV). The inset shows temperature dependence of scattering time \( \tau \) obtained by the fitting. (E) Normalized power spectra of transmitted pump THz pulse for the Cd$_3$As$_2$ film, a reference substrate, and graphene on SiC. (F) THG intensity as a function of the intensity of transmitted fundamental wave \( I \). The solid lines for the Cd$_3$As$_2$ data are fitted results with function \( \propto I^\alpha \) with \( \alpha=2.7 \) and 2.4 for weaker and stronger field, respectively. The graphene data are fitted with \( \propto I^3 \).
Fig. 2. THz pump-THz probe spectroscopy for nonequilibrium dynamics in Cd$_3$As$_2$. (A) Schematic of broadband short THz pump-THz probe spectroscopy. (B) Probe pulse waveform $E_{probe}$ as a function of the probe delay $t_2$. (C) 2D plot of the change of the probe electric field $\delta E_{probe}$ by the THz pump as functions of the pump delay $t_1$ and the probe delay $t_2$. (D) $\delta E_{probe}$ with a fixed delay of $t_2$ at the peak of the probe indicated by the broken line in (C). (E) 2D plot of the real-part conductivity spectra as a function of the frequency and the pump delay $t_1$. (F)(G) Open circles show the real and imaginary parts of the transient conductivity spectra at $t_1=5$ ps in comparison with data in equilibrium. The solid curves show the fitting with the Drude model. (H)(I) The carrier density $N$ and scattering time $\tau$ obtained by the fitting in (F) as a function of the pump delay $t_1$. 
Fig. 3. Dynamics of Dirac electrons during THG process studied by calculation and THz pump-THz probe measurement. (A) Calculated spectra of the THz THG for excitation frequency of $f=0.8$ THz and scattering time $\tau=145$ fs. (B) THG amplitude as a function of the field strength for various $\tau$ for $f=0.8$ THz. The solid line shows a fitting for the perturbative regime. (C) THG amplitude as a function of $\tau$ for $f=0.8$ THz and peak field of 3 and 6 kV/cm. The solid lines show power-law fittings to clearly see saturation. (D) 2D plot of the electron distribution in the momentum space parallel and perpendicular to the pump polarization, as denoted by $k_{\text{pump}}$ and $k_\perp$, respectively. The top and bottom panels correspond to equilibrium and under the field of 6 kV/cm at $f=0.8$ THz. (E) Schematic of monochromatic THz pump-THz probe measurement. (F) The upper figure shows the pump THz pulse waveform with $f=0.8$ THz. The lower figure shows the pump-probe signal $\delta E_{\text{probe}}$ as a function of the pump delay $t_1$ for the probe polarizations parallel and perpendicular to the pump. The data are normalized at the peak value of probe field and shown with offset for clarity. (G) Fourier components of $\delta E_{\text{probe}}$ on the interband excitation signal in (F). The arrow indicates the oscillation component at $2f=1.6$ THz observed only in the parallel polarization configuration. The peak at $f=0.8$ THz is ascribed to an artifact (See Supplementary Materials) (27).
Fig. 4. HHG with mid-IR excitation. (A) Schematics of the HHG measurement with mid-IR excitation in reflection geometry. (B) HHG spectra in visible range. The base substrate GaAs shows odd-order HHG and photoluminescence (PL). The buffer layer GaSb also shows both odd- and even-order HHG. Cd$_3$As$_2$ film on GaSb/GaAs with 280-nm thickness shows stronger odd-order HHG without any PL or even-order signals.